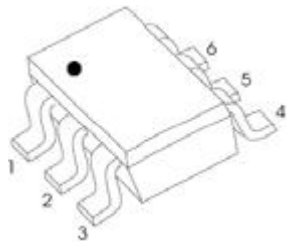
Plastic-Encapsulate Diodes

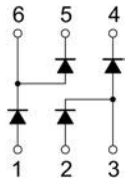
SCHOTTKY BARRIER DIODE ARRAYS

FEATURES

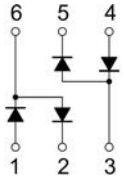
- Low Forward Voltage Drop
- Fast Switching
- Small Surface Mount Package
- PN Junction Guard Ring for Transient and ESD Protection
- Available in Lead Free Version

SOT-363





BAS70BRW



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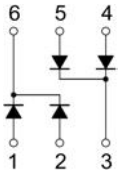

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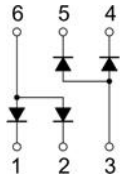

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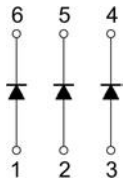
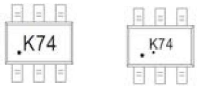
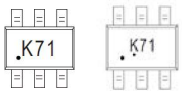
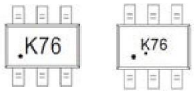
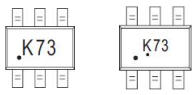


BAS70TW

MARKING:

BAS70BRW	BAS70DW-04	BAS70DW-05	BA S70DW-06	BA S70TW
				

Solid dot = Green molding compound device,if none, the normal device.

Solid dot = Pin1 indicate.

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

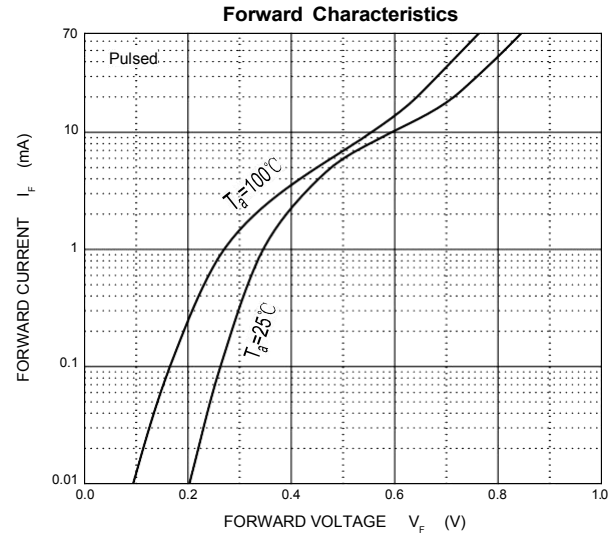
Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	70	V
V_{RWM}	Peak Working Reverse Voltage		
V_R	DC Blocking Voltage		
$V_{R(RMS)}$	RMS Reverse Voltage	49	V
I_O	Forward Continuous Current	70	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @t=8.3ms	100	mA
P_D	Power Dissipation	200	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	500	℃/W
T_j	Operating Junction Temperature Range	-40 ~ +125	℃
T_{stg}	Storage Temperature Range	-55 ~ +150	℃

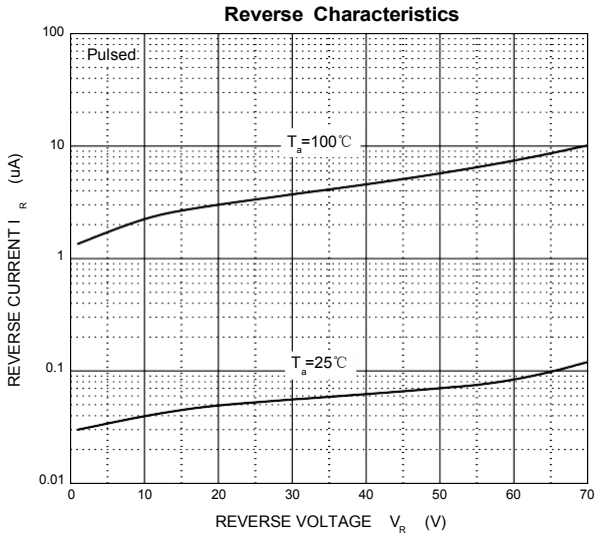
ELECTRICAL CHARACTERISTICS

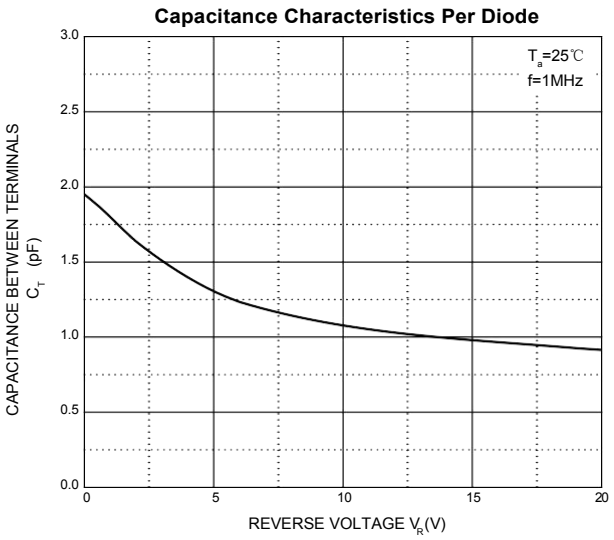
T_a=25 ℃ unless otherwise specified

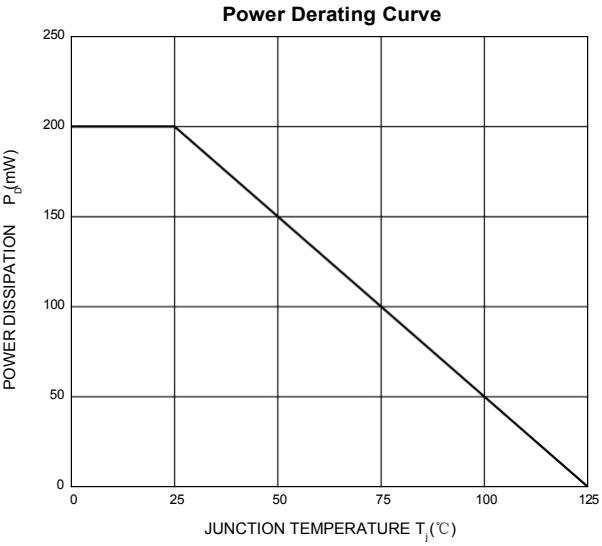
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=10μA	70			V
Reverse current	I_R	V_R=50V			0.1	μA
Forward voltage	V_F	I_F=1mA			0.41	V
		I_F=15mA			1	
Total capacitance	C_{tot}	V_R=0V,f=1MHz			2	pF
Reverse recovery time	t_{rr}	I_F=I_R=10mA to I_R=1mA,I_{rr}=0.1×I_R, R_L=100Ω			5	ns

Typical Characteristics

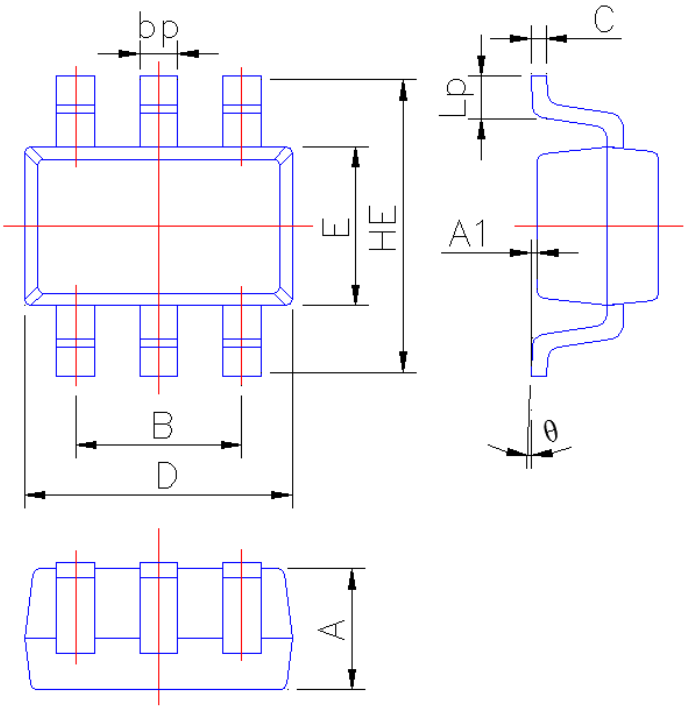








SOT-363 Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°